

L Number	Hits	Search Text	DB	Time stamp
1	570	dislocation and (pn with junction)	USPAT; US-PGPUB	2003.08.28 11:45
2	530	(dislocation and (pn with junction)) and @ad:20020228	USPAT; US-PGPUB	2003.08.28 11:45
3	5	((dislocation and (pn with junction)) and @ad:20020228) and (traversing or traverse)	USPAT; US-PGPUB	2003.08.28 11:45
4	53	dislocation and (pn with junction)	EFC; JPO; DEFWENT; IEM_TDB	2003.08.28 11:45
5	0	(dislocation and (pn with junction)) and (traversing or traverse)	EFC; JPO; DEFWENT; IEM_TDB	2003.08.28 11:46

DERWENT-ACC-NO: 1981-17631D

DERWENT-WEEK: 198111

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TITLE: Quasi-unidirectional pn junctions
mfr. - by contacting emerging dislocations in
semiconductor volume

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PATENT-ASSIGNEE: HERRMANN R[HERRI]

PRIORITY-DATA: 1979DD-0215033 (August 17, 1979)

PATENT-FAMILY:

PUB-NO	PAGES	PUB-DATE	
LANGUAGE		MAIN-IPC	
DD 145582 A		December 17, 1980	N/A
000	N/A		

INT-CL (IPC): H01L021/18, H01L029/32

ABSTRACTED-PUB-NO: DD 145582A

BASIC-ABSTRACT:

Quasi-unidimensional p-n junctions are produced in solids, esp. in semiconductors where the type of conduction of the dislocations differs from that of the semiconductor volume. The contacts are applied to these dislocations at their emergence area and to the semiconductor volume material at a zone free from dislocations; this zone can lie parallel to the dislocations if they are in parallel.

This utilisation of existing or created dislocations and their contacting provides another incentive for utilising such pn- junctions in the national

economy.

TITLE-TERMS: QUASI UNIDIRECTIONAL PN JUNCTION MANUFACTURE
CONTACT EMERGENCE

DISLOCATE SEMICONDUCTOR VOLUME

DERWENT-CLASS: L03 U11 U12

CPI-CODES: L03-D03; L03-D04;

EPI-CODES: U11-C; U12-E01;